

The oxidation/diffusion clean for silicon wafers consist of three chemical baths. SC1 for residual organics, SC2 for metal impurities and HF dip to remove any native oxide.

SC1 bath

mixture 5:1:0.5 H₂O:H₂O₂:NH₄OH

time=10min; temp=70C

SC2 bath

mixture 6:1:1 H₂O:H₂O₂:HCL

time=15min; temp=70C

Procedure

- 1) SC1 bath
- 2) DI water rinse
- 3) brief soak in 50:1 H₂O:HF (HF dip) at RT for ~15seconds
- 4) brief DI water rinse
- 5) SC2 bath
- 6) DI water rinse
- 7) SRD rinse/dry